

## Thyristor High Voltage, Phase Control SCR, 50 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub> 50 A					
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V				
V <sub>TM</sub> (typ.)	1.2 V				
I <sub>GT</sub> (typ.)	40 mA				
T <sub>J</sub> max.	125 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

#### **FEATURES**

- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification



- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

#### **DESCRIPTION**

The VS-50TPS12 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V <sub>RRM</sub> / V <sub>DRM</sub>		1200	V			
On-state voltage	V <sub>T</sub>	50 A, T <sub>J</sub> = 125 °C	1.2	V			
Average rectified forward current	I <sub>T(AV)</sub>		50				
Maximum continuous RMS on-state current	I <sub>RMS</sub>		79	Α			
Non-repetitive peak surge current	I <sub>TSM</sub>		630				
Maximum rate of rise	dv/dt		1000	V/µs			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> / V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> / I <sub>DRM</sub> AT 125 °C mA				
VS-50TPS12LHM3	1200	1300	10				



PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_C = 82$ °C, 180° conduction half sine wa	ave	-	50	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			-	79	Α
Peak, one-cycle non-repetitive surge current	L	10 ms sine pulse, rated V <sub>RRM</sub> applied		-	530	
reak, one-cycle non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied	Initial $T_J = T_J$	-	630	
I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	maximum	-	1405	A <sup>2</sup> s
I-t for fusing	I-l	10 ms sine pulse, no voltage reapplied		-	1986	A-S
$I^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C		-	19 850	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	T 405 90		-	0.89	V
High level value of threshold voltage	V <sub>T(TO)2</sub>			-	0.97	
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C		-	6.77	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>				6.32	1115.2
On-state voltage	V	50 A, T <sub>J</sub> = 25 °C		1.2	1.32	V
On-State voltage	$V_{T}$	100 A, T <sub>J</sub> = 25 °C			1.6	V
Rate of rise of turned-on current	di/dt	T <sub>J</sub> = 25 °C		-	150	A/µs
Holding current	Ι <sub>Η</sub>	Anada ayyahı CV yaşistiya land T. 05 %C		-	300	
Latching current	ال	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		-	350	Л
Powers and direct lookage current	1 /1	T <sub>J</sub> = 25 °C		-	0.05	mA
Reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	T <sub>J</sub> = 125 °C			10	
		$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_q$ - $k = \infty \Omega$				

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Peak gate power	P <sub>GM</sub>	10 ma sina nula	se, no voltage reapplied	-	10	W
Average gate power	P <sub>G(AV)</sub>	TO THIS SITTLE PURS	se, no voltage reapplied	-	2.5	VV
Peak gate current	I <sub>GM</sub>			-	2.5	Α
Peak negative gate voltage	-V <sub>GM</sub>			-	10	
		T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	-	1.6	V
Required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		-	1.5	]
		T <sub>J</sub> = 125 °C	Г <sub>J</sub> = 125 °C		1.1	
		T <sub>J</sub> = -40 °C		-	160	
Required DC gate to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	45	100	mA
		T <sub>J</sub> = 125 °C		-	70	
DC gate voltage not to trigger	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value			0.25	V
DC gate current not to trigger	I <sub>GD</sub>	$I_{J} = 125  {}^{5}\text{C}, V_{D}$		4.5	mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t <sub>gt</sub>	$I_T = 50 \text{ A}, V_D = 50 \% V_{DRM}, I_{gt} = 300 \text{ mA}, T_J = 25 °C$	1.5	ı	
Turn-off time	t <sub>q</sub>	$I_T$ = 50 A, $V_D$ = 80 % $V_{DRM}$ , $dV/dt$ = 20 $V/\mu s$ , $t_p$ = 200 $\mu s$ $I_{gt}$ = 100 mA, $dI/dt$ = 10 A/ $\mu s$ , $V_R$ = 100 V, $T_J$ = 125 °C	85	-	μs



THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Maximum junction and storage ten	nperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40	125	°C		
Maximum thermal resistance, junction to case		$R_{thJC}$		-	0.35			
Maximum thermal resistance, junction to ambient		$R_{thJA}$		-	40	°C/W		
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.2	-			
minimum				6	(5)	kgf · cm		
Mounting torque	maximum			12	(10)	(lbf · in)		
Marking device			Case style Super TO-247AD 3L	;	50TPS12L	Н		

△R <sub>thJ-HS</sub> CONDUCTION PER JUNCTION											
DEVICE	S	SINE HALF-WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				UNITS
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-50TPS12LHM3	0.143	0.166	0.208	0.299	0.490	0.099	0.168	0.223	0.311	0.494	°C/W

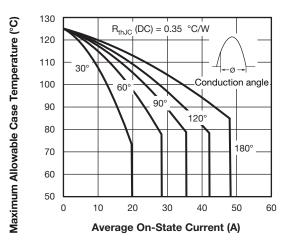


Fig. 1 - Current Rating Characteristics

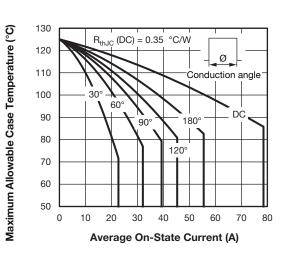


Fig. 2 - Current Rating Characteristics

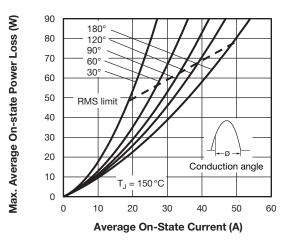


Fig. 3 - On-State Power Loss Characteristics

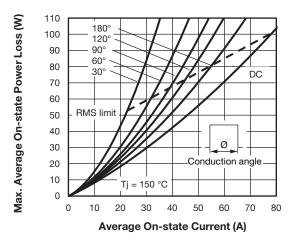


Fig. 4 - On-State Power Loss Characteristics

Revision: 23-Feb-18

### Vishay Semiconductors

Document Number: 96108

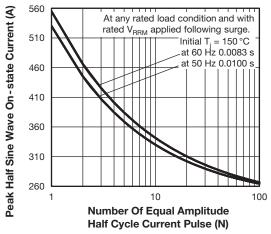


Fig. 5 - Maximum Non-Repetitive Surge Current

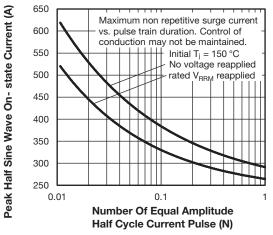


Fig. 6 - Maximum Non-Repetitive Surge Current

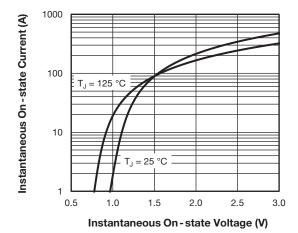
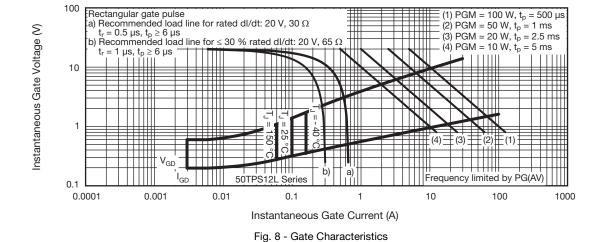


Fig. 7 - On-State Voltage Drop Characteristics



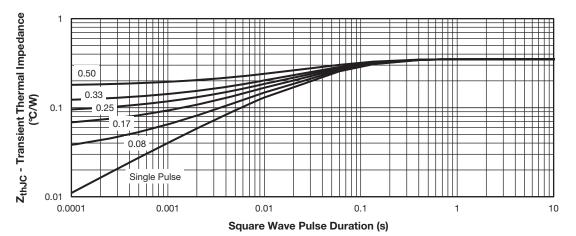
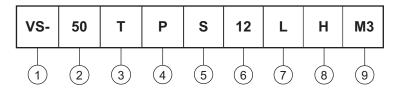


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



- 1 Vishay Semiconductors product
- 2 Current code (50 = 50 A)
- 3 Circuit configuration:
  - T = thyristor
- 4 P = TO-247AD package
- 5 Type of silicon:

S = standard recovery rectifier

- 6 Voltage code (12 = 1200 V)
- 7 Package L = long lead
- 8 H = AEC-Q101 qualified
- 9 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-50TPS12LHM3	25	contact factory	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS							
Dimensions TO-247AD 3L <u>www.vishay.com/doc?95626</u>							
Part marking information TO-247AD 3L <u>www.vishay.com/doc?95007</u>							



### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.